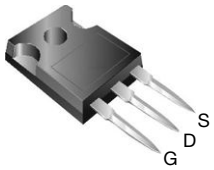
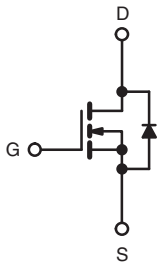
S Series Power MOSFET

PRODUCT SUMMARY		
V_{DS} at T_J max. (V)	650	
$R_{DS(on)}$ max. at 25 °C (Ω)	V_{GS} = 10 V	0.190
Q_g max. (nC)	98	
Q_{gs} (nC)	17	
Q_{gd} (nC)	25	
Configuration	Single	

TO-247AC





N-Channel MOSFET

FEATURES

- Generation One
- **Halogen-free According to IEC 61249-2-21 Definition**
- High E_{AR} Capability
- Lower Figure-of-Merit R_{on} x Q_g
- 100 % Avalanche Tested
- Ultra Low R_{on}
- dV/dt Ruggedness
- Ultra Low Gate Charge (Q_g)
- Compliant to RoHS Directive 2002/95/EC

RoHS* COMPLIANT

HALOGEN FREE Available

Note

* Pb containing terminations are not RoHS compliant, exemptions may apply

APPLICATIONS

- PFC Power Supply Stages
- Hard Switching Topologies
- Solar Inverters
- UPS
- Motor Control
- Lighting
- Server Telecom

ORDERING INFORMATION	
Package	TO-247AC
Lead (Pb)-free	SiHG22N60S-E3
Lead (Pb)-free and Halogen-free	SiHG22N60S-GE3

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	600	V
Gate-Source Voltage			V_{GS}	± 20	
Gate-Source Voltage AC (f > 1 Hz)				30	
Continuous Drain Current	V_{GS} at 10 V	T_C = 25 °C	I_D	22	A
		T_C = 100 °C		13	
Pulsed Drain Current[a]			I_{DM}	65	
Linear Derating Factor		TO-247		2	W/°C
Single Pulse Avalanche Energy[b]			E_{AS}	690	mJ
Repetitive Avalanche Energy[a]			E_{AR}	25	
Maximum Power Dissipation		TO-247	P_D	250	W
Drain-Source Voltage Slope	T_J = 125 °C		dV/dt	37	V/ns
Reverse Diode dV/dt[d]				5.3	
Operating Junction and Storage Temperature Range			T_J, T_{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)[c]	for 10 s			300	

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature.

b. V_{DD} = 50 V, starting T_J = 25 °C, L = 28.2 mH, R_g = 25 Ω, I_{AS} = 7 A.

c. 1.6 mm from case.

d. $I_{SD} \leq I_D$, dI/dt = 100 A/µs, starting T_J = 25 °C.

THERMAL RESISTANCE RATINGS					
PARAMETER		**SYMBOL**	**TYP.**	**MAX.**	**UNIT**
Maximum Junction-to-Ambient	TO-247	R_{thJA}	-	62	°C/W
Maximum Junction-to-Case (Drain)	TO-247	R_{thJC}	-	0.5	

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 1 mA		600	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 1 mA		-	0.70	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA		2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	V_{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 600 V, V_{GS} = 0 V		-	-	1	µA
		V_{DS} = 600 V, V_{GS} = 0 V, T_J = 150 °C		-	-	100	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 11 A	-	0.160	0.190	Ω
Forward Transconductance[a]	g_{fs}	V_{DS} = 50 V, I_D = 13 A		-	9.4	-	S
Dynamic							
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1.0 MHz		-	2810	-	pF
Output Capacitance	C_{oss}			-	1480	-	
Reverse Transfer Capacitance	C_{rss}			-	33	-	
Effective Output Capacitance (Time Related)	$C_{oss\ eff.}$ (TR)[a]	V_{GS} = 0 V	V_{DS} = 0 V to 480 V	-	155	-	
Total Gate Charge	Q_g	V_{GS} = 10 V	I_D = 22 A, V_{DS} = 480 V	-	75	110	nC
Gate-Source Charge	Q_{gs}			-	17	-	
Gate-Drain Charge	Q_{gd}			-	25	-	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 380 V, I_D = 22 A, R_g = 9.1 Ω, V_{GS} = 10 V		-	24	50	ns
Rise Time	t_r			-	68	100	
Turn-Off Delay Time	$t_{d(off)}$			-	77	115	
Fall Time	t_f			-	59	90	
Gate Input Resistance	R_g	f = 1 MHz, open drain		-	0.65	-	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	22	A
Pulsed Diode Forward Current	I_{SM}			-	-	88	
Diode Forward Voltage	V_{SD}	T_J = 25 °C, I_S = 22 A, V_{GS} = 0 V		-	-	1.2	V
Reverse Recovery Time	t_{rr}	T_J = 25 °C, I_F = I_S, dI/dt = 100 A/µs, V_R = 25 V		-	462	690	ns
Reverse Recovery Charge	Q_{rr}			-	8.3	16	µC
Reverse Recovery Current	I_{RRM}			-	30	60	A

Note

a. $C_{oss\ eff.}$ (TR) is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS}.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

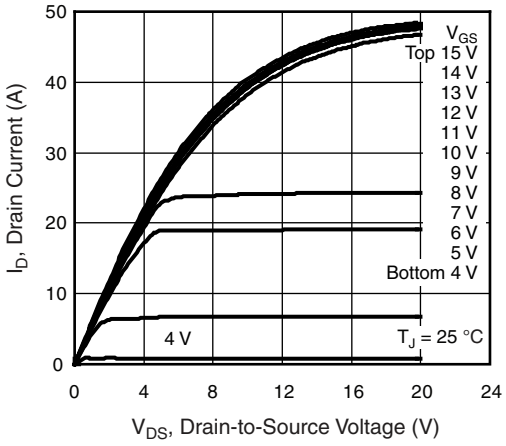


Fig. 1 - Typical Output Characteristics, T_J = 25 °C

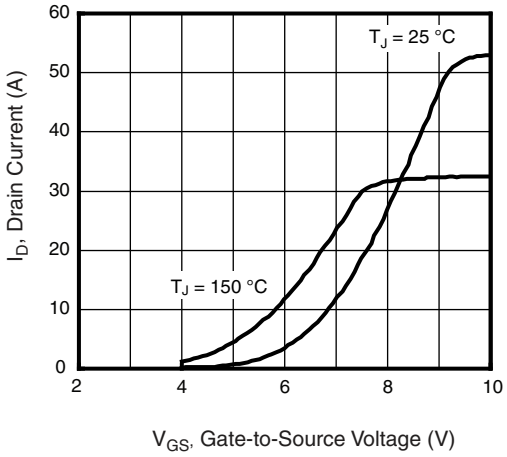


Fig. 3 - Typical Transfer Characteristics

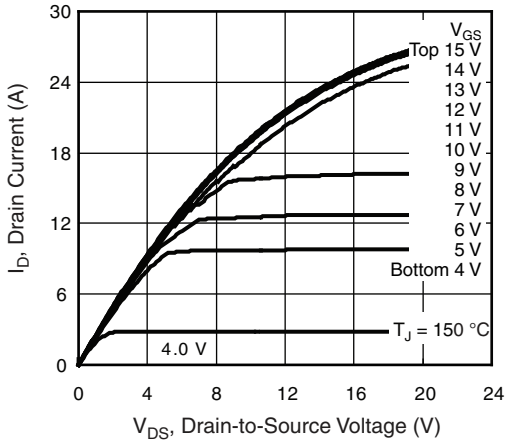


Fig. 2 - Typical Output Characteristics, T_J = 150 °C

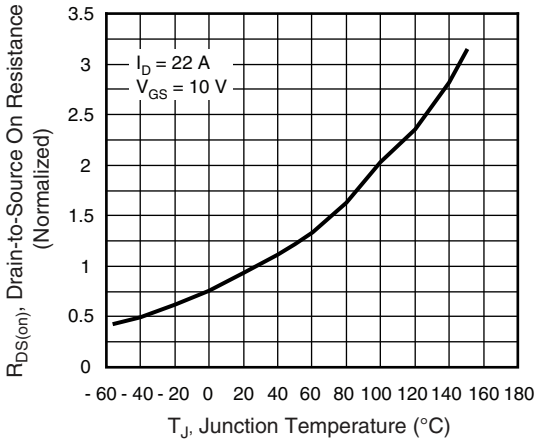


Fig. 4 - Normalized On-Resistance vs. Temperature

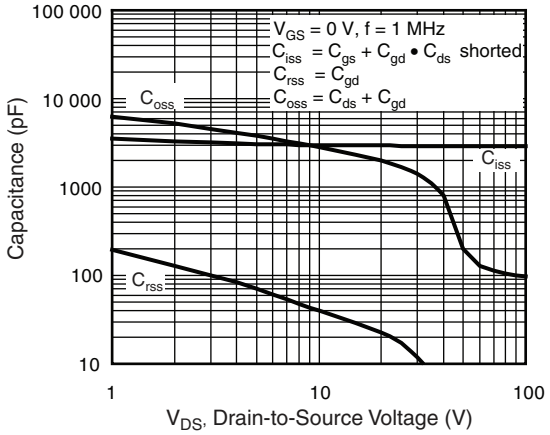


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

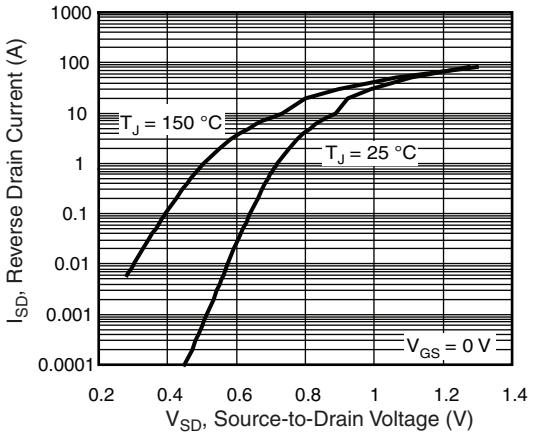


Fig. 7 - Typical Source-Drain Diode Forward Voltage

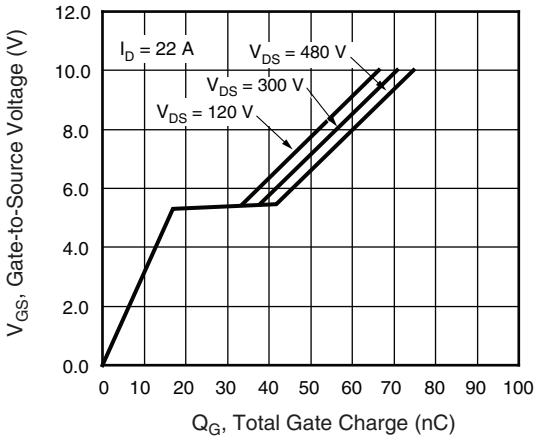


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

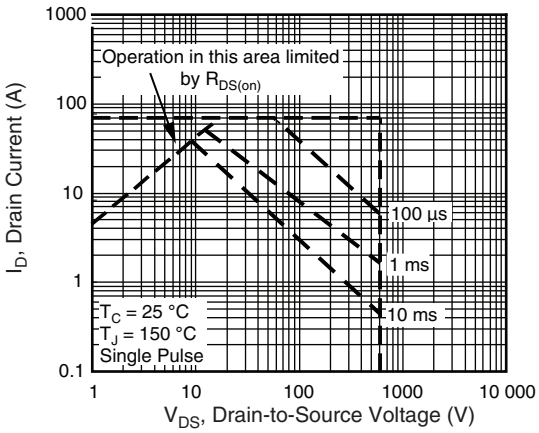


Fig. 8 - Maximum Safe Operating Area

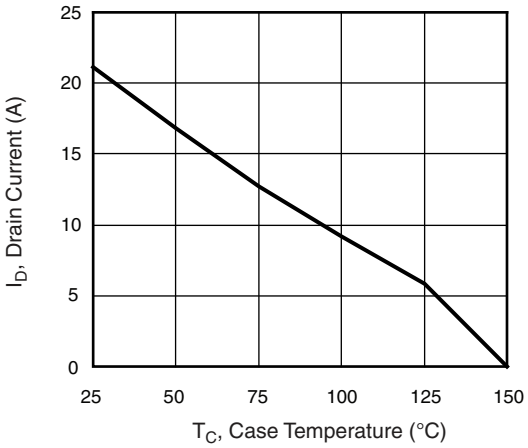


Fig. 9 - Maximum Drain Current vs. Case Temperature

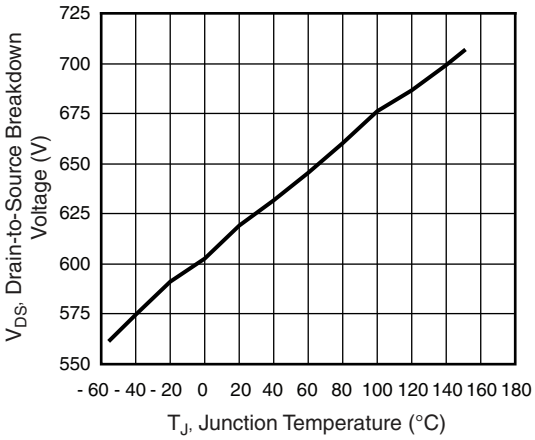


Fig. 10 - Drain-to-Source Breakdown Voltage

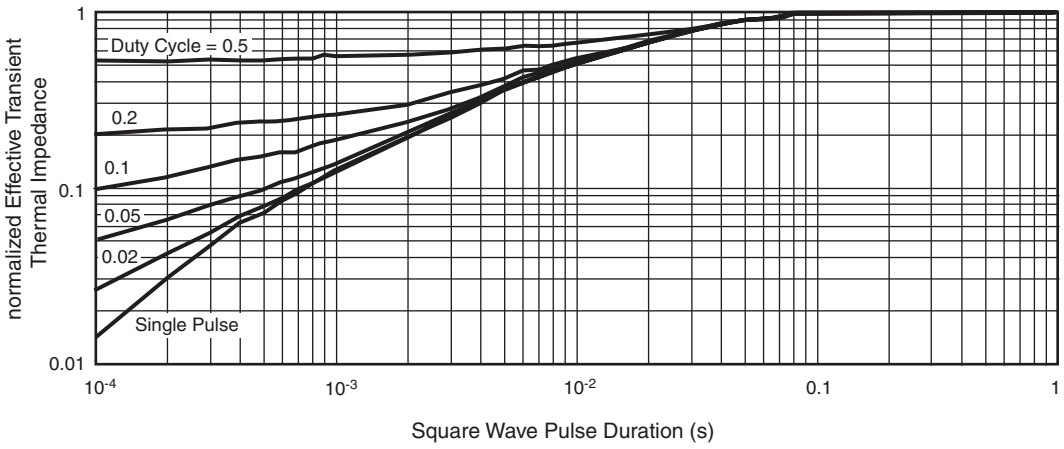


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case

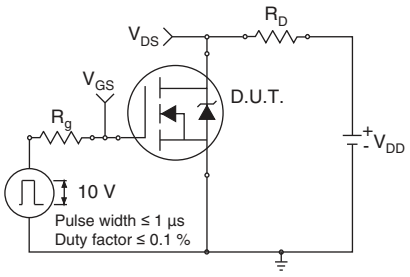


Fig. 11a - Switching Time Test Circuit

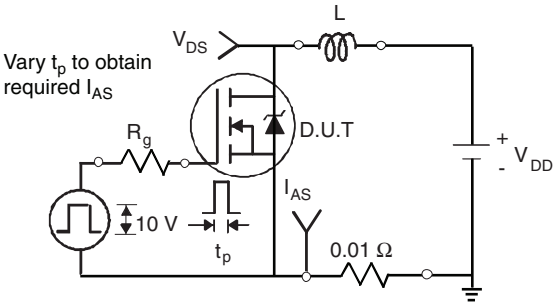


Fig. 12a - Unclamped Inductive Test Circuit

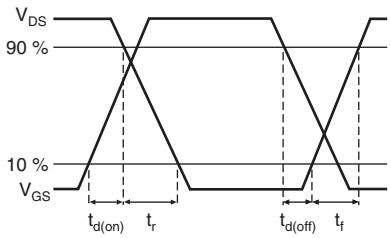


Fig. 11b - Switching Time Waveforms

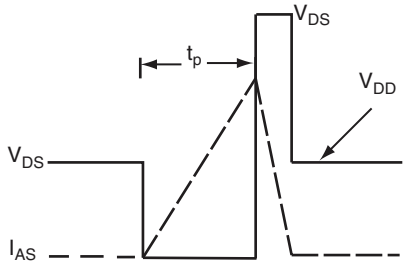


Fig. 12b - Unclamped Inductive Waveforms

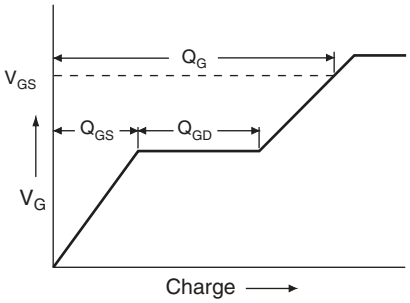


Fig. 13a - Basic Gate Charge Waveform

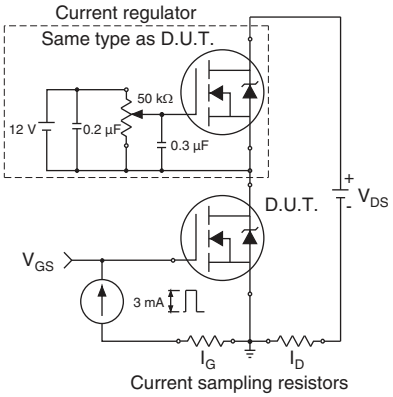
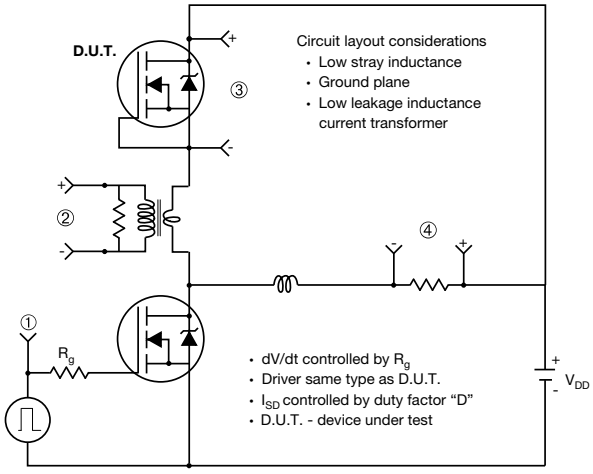
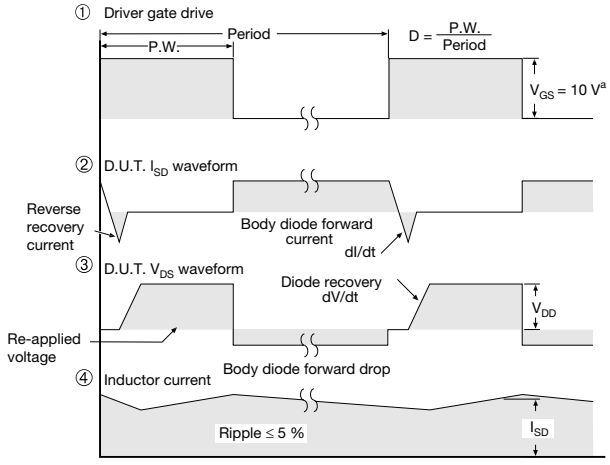


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit





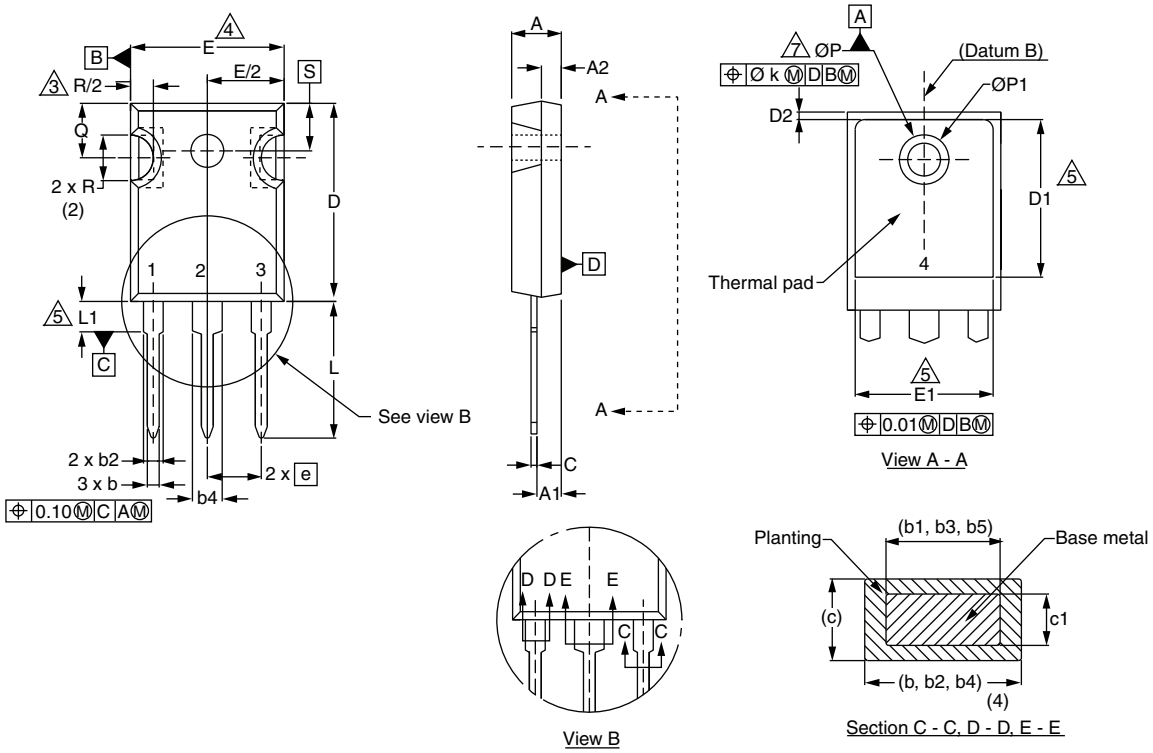
Note

a. V_{GS} = 5 V for logic level devices

Fig. 14 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91393.

TO-247AC (High Voltage)



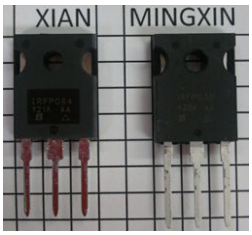
	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	4.58	5.31	0.180	0.209
A1	2.21	2.59	0.087	0.102
A2	1.17	2.49	0.046	0.098
b	0.99	1.40	0.039	0.055
b1	0.99	1.35	0.039	0.053
b2	1.53	2.39	0.060	0.094
b3	1.65	2.37	0.065	0.093
b4	2.42	3.43	0.095	0.135
b5	2.59	3.38	0.102	0.133
c	0.38	0.86	0.015	0.034
c1	0.38	0.76	0.015	0.030
D	19.71	20.82	0.776	0.820
D1	13.08	-	0.515	-

	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D2	0.51	1.30	0.020	0.051
E	15.29	15.87	0.602	0.625
E1	13.72	-	0.540	-
e	5.46 BSC		0.215 BSC	
Ø k	0.254		0.010	
L	14.20	16.25	0.559	0.640
L1	3.71	4.29	0.146	0.169
N	7.62 BSC		0.300 BSC	
Ø P	3.51	3.66	0.138	0.144
Ø P1	-	7.39	-	0.291
Q	5.31	5.69	0.209	0.224
R	4.52	5.49	0.178	0.216
S	5.51 BSC		0.217 BSC	

ECN: X12-0167-Rev. B, 24-Sep-12
DWG: 5971

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Contour of slot optional.
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body.
4. Thermal pad contour optional with dimensions D1 and E1.
5. Lead finish uncontrolled in L1.
6. Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154").
7. Outline conforms to JEDEC outline TO-247 with exception of dimension c.
8. Xian and Mingxin actually photo.



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, “Vishay”), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay’s knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer’s responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer’s technical experts. Product specifications do not expand or otherwise modify Vishay’s terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk and agree to fully indemnify and hold Vishay and its distributors harmless from and against any and all claims, liabilities, expenses and damages arising or resulting in connection with such use or sale, including attorneys fees, even if such claim alleges that Vishay or its distributor was negligent regarding the design or manufacture of the part. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.